1.5V Drive Pch MOSFET

RZL025P01

Structure

Silicon P-channel MOSFET

Features

1) Low on-resistance.

- 2) High power package.
- 3) Low voltage drive. (1.5V)

Application

Switching

Packaging specifications

	Package	Taping		
Туре	Code	TR		
	Basic ordering unit (pieces)	3000		
RZL025P01		0		

•Dimensions (Unit : mm)



Equivalent circuit



Absolute maximum ratings (Ta=25°C)

	U (,			
Parameter		Symbol	Limits	Unit	
Drain-source voltage		VDSS	-12	V	
Gate-source voltage		Vgss	±10	V	
Ducia cumunt	Continuous	lь	±2.5	A	
Drain current	Pulsed	IDP *1	±10	А	
Source current	Continuous	ls	-0.8	A	
(Body diode)	Pulsed	Isp *1	-10	А	
Total power dissipation		P _D *2	1.0	W	
Channel temperature		Tch	150	°C	
Range of Storage temperature		Tstg	-55 to +150	°C	
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*1 Pw≤10μs, Duty cycle≤1% *2 Mounted on a ceramic board

Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a) *	125	°C / W

* When mounted on a ceramic board.

Transistors

•Electrical characteristics (Ta=25°C)

Symbol	Min.	Тур.	Max.	Unit	Conditions
Igss	-	-	±10	μA	V _{GS} =±10V, V _{DS} =0V
V(BR) DSS	-12	-	-	V	I _D = -1mA, V _{GS} =0V
IDSS	-	-	-1	μΑ	V_{DS} = -12V, V_{GS} =0V
VGS (th)	-0.3	-	-1.0	V	$V_{DS} = -6V$, $I_{D} = -1mA$
RDS (on)*	-	44	61	mΩ	I _D = -2.5A, V _{GS} = -4.5V
	-	60	84	mΩ	I _D = -1.2A, V _{GS} = -2.5V
	-	81	121	mΩ	I _D = -1.2A, V _{GS} = -1.8V
	-	110	220	mΩ	ID= -0.5A, VGs= -1.5V
Yfs *	3.5	-	-	S	Vps= -6V, Ip= -2.5A
Ciss	_	1350	-	pF	V _{DS} = -6V
Coss	-	130	-	pF	V _{GS} =0V
Crss	-	125	-	pF	f=1MHz
td (on) *	-	9	-	ns	ID= -1.2A
tr *	-	35	-	ns	VDD≒ –6V VGS= –4.5V
td (off) *	-	130	-	ns	VGS = -4.5V $RL = 5\Omega$
t _f *	-	85	_	ns	Rg=10Ω
Qg *	-	13	-	nC	V _{DD} ≒-6V, I _D =-2.5A
Qgs *	-	2.5	-	nC	Vgs=-4.5V
Q _{gd} *	-	2.0	-	nC	RL≒ 2.4Ω, RG=10Ω
	V(BR) DSS IDSS VGS (th) RDS (on)* (Yfs) * Ciss Coss Crss td (on) * td (off) * tf * Qg * Qgs *	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

•Body diode characteristics(Source-drain) (Ta=25°C)

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Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V _{SD} *	-	-	-1.2	V	Is= -2.5A, V _{GS} =0V

* Pulsed

Transistors





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Transistors

Measurement circuits



Fig.15 Switching Time Test Circuit



Fig.16 Switching Time Waveforms



Fig.17 Gate Charge Test Circuit



Fig.18 Gate Charge Waveform

Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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Appendix1-Rev2.0

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